

-30V/-6.5A P-Channel MOSFET

Features

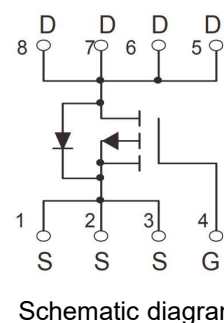
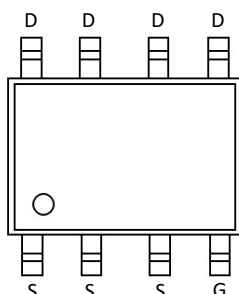
- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
-30V	46m Ω @-10V	-6.5A
	72m Ω @-4.5V	

Application

- Battery protection
- Power management
- Load switch



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

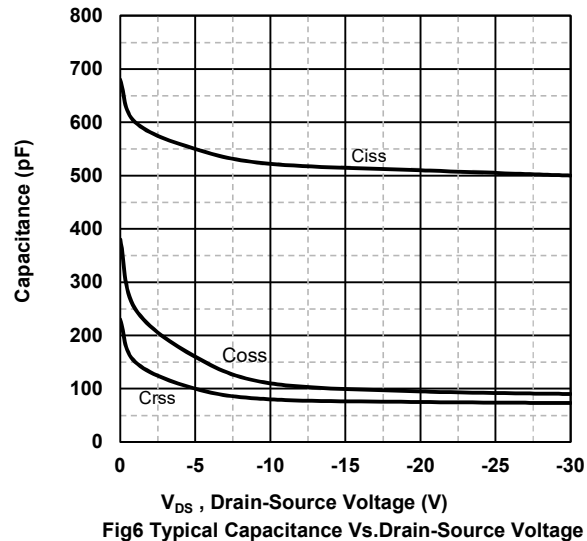
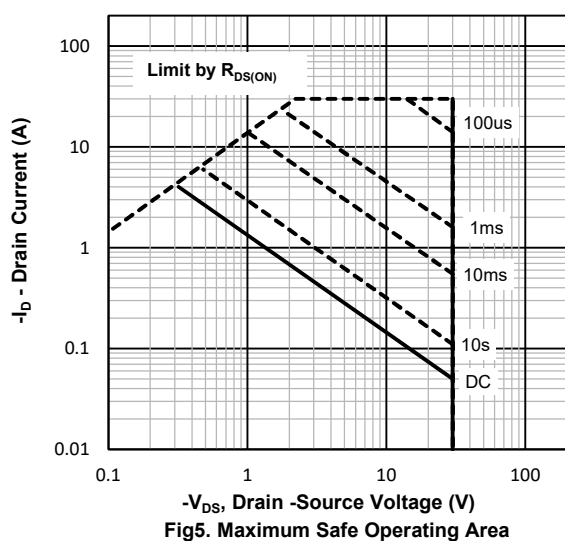
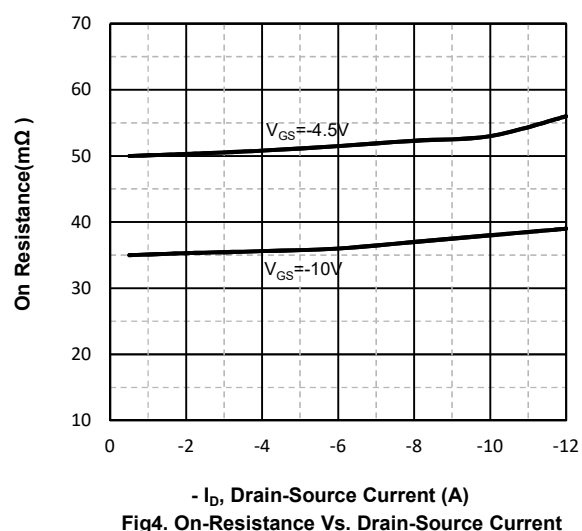
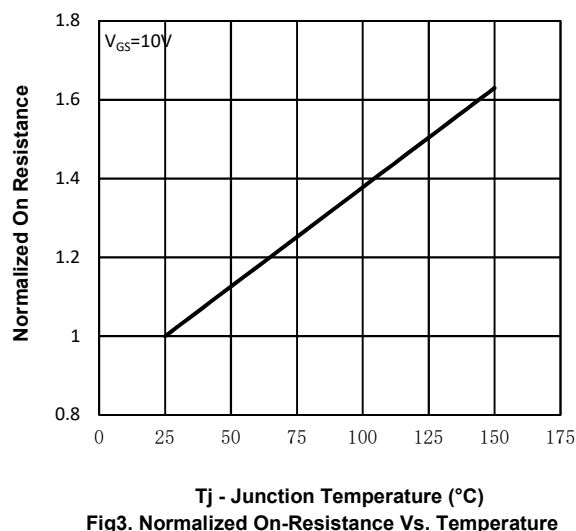
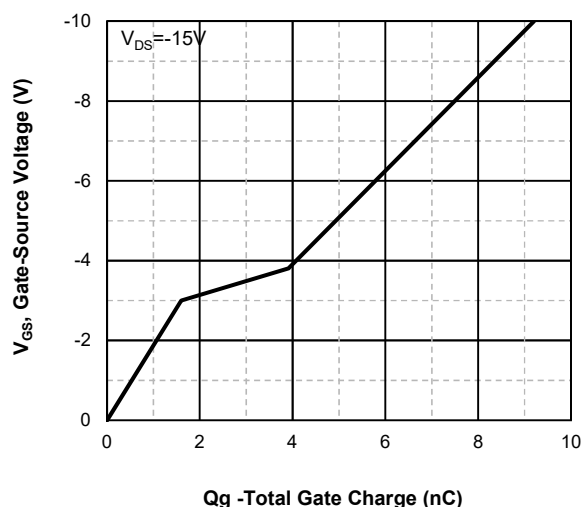
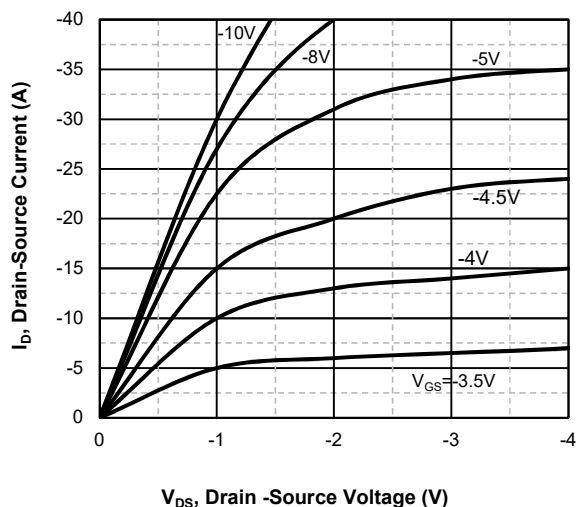
V _{DS}	Drain-Source Breakdown Voltage		-30	V
V _{GS}	Gate-Source Voltage		±20	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	-6.5	A

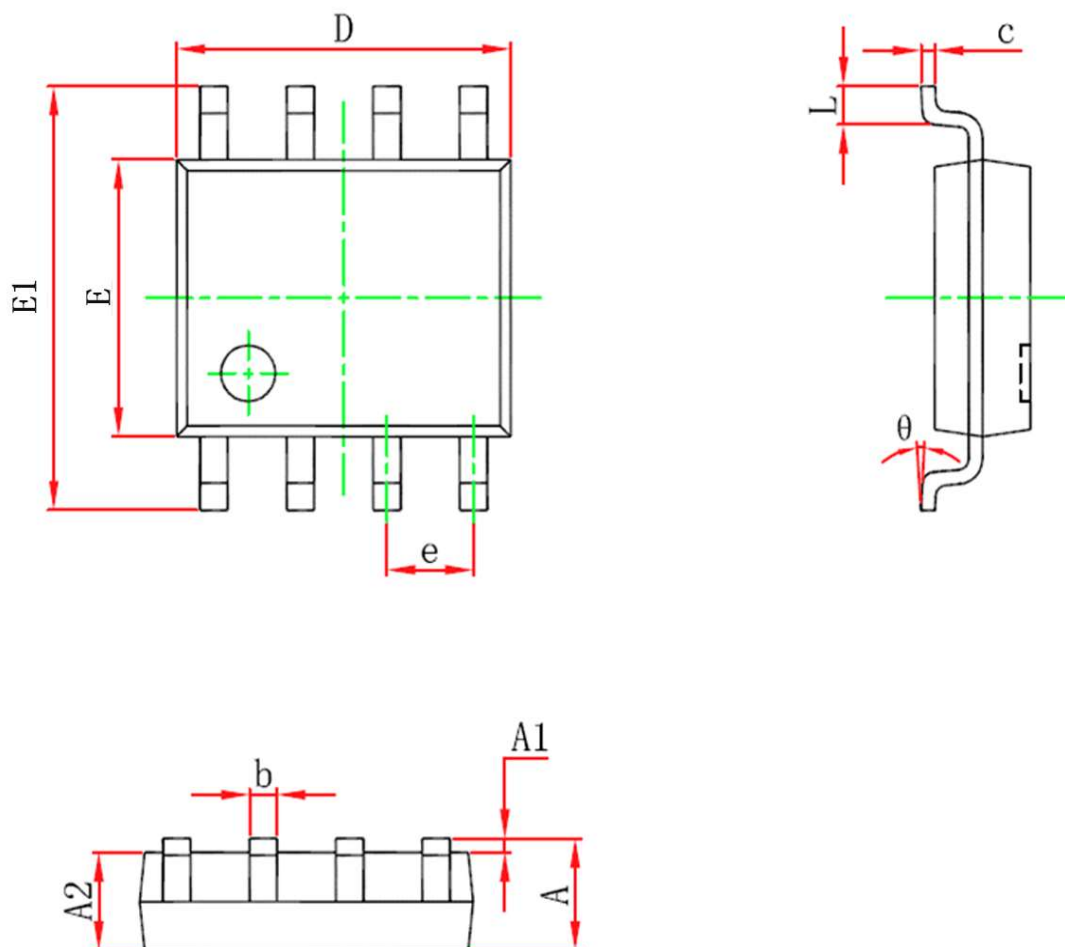
Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$	-30	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$	-6.5	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	3.1	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		40	°C/W

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=-250μA	-30	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-30V, VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=-250μA	-1	-1.8	-3	V
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-6.5A	--	33	46	mΩ
		VGS=-4.5V, ID=-5A	--	50	72	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
CISS	Input Capacitance	VDS=-15V, VGS=0V, f=1MHz	--	520	--	pF
COSS	Output Capacitance		--	100	--	pF
CRSS	Reverse Transfer Capacitance		--	65	--	pF
Switching Characteristics						
Qg	Total Gate Charge	VDS=-15V, ID=-6.5A, VGS=-10V	--	9.2	--	nC
Qgs	Gate Source Charge		--	1.6	--	nC
Qgd	Gate Drain Charge		--	2.2	--	nC
td(on)	Turn-on Delay Time	VDD=-15V, ID=-6.5A, VGS=-10V, RG=3Ω	--	7.5	--	nS
tr	Turn-on Rise Time		--	5.5	--	nS
td(off)	Turn-Off Delay Time		--	19	--	nS
tf	Turn-Off Fall Time		--	7	--	nS
Source- Drain Diode Characteristics						
VSD	Forward on voltage	TJ=25°C, IS=-6.5A	--	-0.8	-1.2	V

Typical Operating Characteristics



SOP-8 Package information


Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.450	1.750	0.057	0.068
A1	0.100	0.250	0.003	0.009
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.012	0.020
c	0.170	0.250	0.006	0.009
D	4.700	5.100	0.185	0.200
e	1.270(BSC)		0.050(BSC)	
E	3.800	4.000	0.149	0.157
E1	5.800	6.200	0.228	0.244
L	0.400	1.270	0.015	0.050
θ	0°	8°	0°	8°